2N6660

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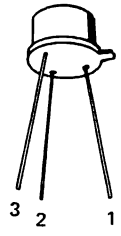
N-Channel Enhancement Mode
MOSPOWER

APPLICATIONS

- Switching Regulators
- Converters
- Motor Drivers

PIN 1 – Source
PIN 2 – Gate
PIN 3 & CASE – Drain



TO–205AF (TO–39)

PRODUCT SUMMARY

Part Number	BV_{DSS} Volts	$r_{DS(ON)}$ (ohms)	Package
2N6660	60	3	TO–205AF

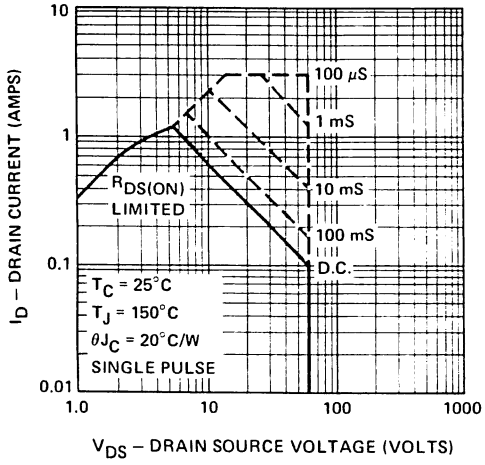
For Additional Curves
See Section 5: VNMA06

ABSOLUTE MAXIMUM RATINGS (T_C = 25° C unless otherwise noted)

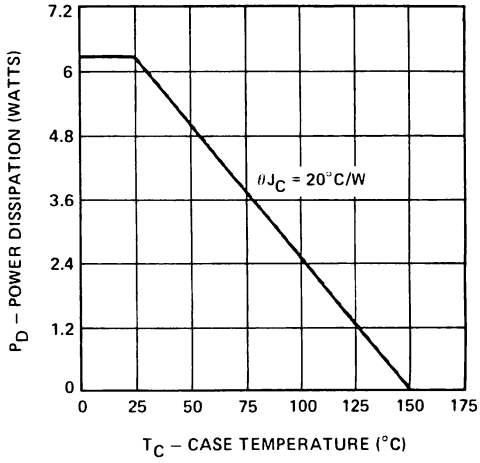
	Parameter	2N6660	Units
V_{DS}	Drain-Source Voltage	60	V
V_{DGR}	Drain-Gate Voltage (R_{GS} = 1 MΩ)	60	V
I_D @ T_C = 25° C	Continuous Drain Current	±1.1	A
I_D @ T_C = 100° C	Continuous Drain Current	±0.8	A
I_{DM}	Pulsed Drain Current[1]	±3	A
V_{GS}	Gate-Source Voltage	±40	V
P_D @ T_C = 25° C	Max. Power Dissipation	6.25	W
P_D @ T_C = 100° C	Max. Power Dissipation	2.5	W
Junction to Case	Linear Derating Factor	0.05	W/° C
Junction to Ambient	Linear Derating Factor	0.006	W/° C
T_J Tstg	Operating and Storage Temperature Range	−55 To +150	° C
Lead Temperature	(1/16" from case for 10 secs.)	300	° C

1 **Pulse Test:** Pulsewidth ≤ 300μsec, Duty Cycle ≤ 2%

Active Region



Power Derating



ELECTRICAL CHARACTERISTICS (T_C = 25° C unless otherwise noted)

STATIC

Parameter		Type	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain-Source Breakdown Voltage	2N6660	60	100		V	V_{GS} = 0 I_D = 10 μA
$V_{GS(th)}$	Gate-Threshold Voltage	2N6660	0.8	1.5	2	V	V_{DS} = V_{GS}, I_D = 1 mA
I_{GSSF}	Gate-Body Leakage Forward	2N6660		1 5	100 500	nA	V_{GS} = +15V, V_{DS} = 0 V_{GS}=+15V, V_{DS} = 0, T_A=125° C
I_{GSSR}	Gate-Body Leakage Reverse	2N6660		−1	−100	nA	V_{GS} = −15V, V_{DS} = 0
I_{DSS}	Zero Gate Voltage Drain Current	2N6660		1	10	μA	V_{DS} = Max. Rating, V_{GS} = 0
		2N6660		50	500	μA	V_{DS} = 0.8 Max. Rating, V_{GS} = 0 T_C = 125° C
$I_{D(on)}$	On-State Drain Current[1]	2N6660	1.5	1.7		A	V_{DS}≥2$V_{DS(ON)}$, V_{GS} = 10V
$V_{DS(on)}$	Static Drain-Source On-State Voltage[1]	2N6660		1.4	1.5	V	V_{GS} = 5V , I_D = 0.3A
		2N6660		2.7	3	V	V_{GS} = 10V , I_D = 1A
$R_{DS(on)}$	Static Drain-Source On-State Resistance[1]	2N6660		4.7	5	Ω	V_{GS} = 5V , I_D = 0.3A
		2N6660		2.7	3	Ω	V_{GS} = 10V , I_D = 1A
$R_{DS(on)}$	Static Drain-Source On-State Resistance[1]	2N6660		3.9	4.2	Ω	V_{GS} =10V, I_D =1A , T_C =125° C

DYNAMIC

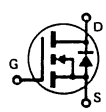
g_{fs}	Forward Transductance[1]	2N6660	170	195		mS	V_{DS} = 25V, I_D = 0.5A
C_{iss}	Input Capacitance	2N6660		35	50	pF	V_{GS} = 0 , V_{DS} = 25V f = 1 MHz
C_{oss}	Output Capacitance	2N6660		33	40	pF	
C_{rss}	Reverse Transfer Capacitance	2N6660		2	10	pF	
t_{ON}	Turn-On Time	2N6660		8	10	ns	V_{DD} = 25V , I_D ≅ 1A R_g = 25Ω , R_L = 23Ω (MOSFET switching times are essentially independent of operating temperature.)
t_{OFF}	Turn-Off Time	2N6660		8	10	ns	

THERMAL RESISTANCE

R_{thJC}	Junction-to-Case	2N6660			20	°C/W	
R_{thJA}	Junction-to-Ambient	2N6660			170	°C/W	Free Air Operation

BODY-DRAIN DIODE RATINGS AND CHARACTERISTICS

I_S	Continuous Source Current (Body Diode)	2N6660			−1.1	A	Modified MOSPOWER symbol showing the integral P-N Junction rectifier
I_{SM}	Source Current[1] (Body Diode)	2N6660			−3	A	
V_{SD}	Diode Forward Voltage[1]	2N6660		−0.9		V	T_C=25° C, I_S=−1.1A, V_{GS} = 0



1 **Pulse Test:** Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%

TYPICAL PERFORMANCE CURVES (25° C unless otherwise noted)

FIGURE 1. Ohmic Region

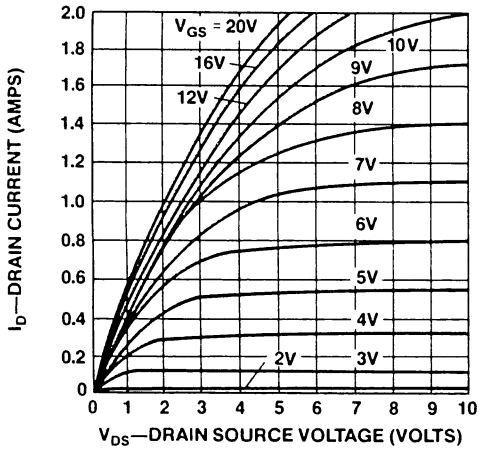


FIGURE 2. Transfer Characteristics

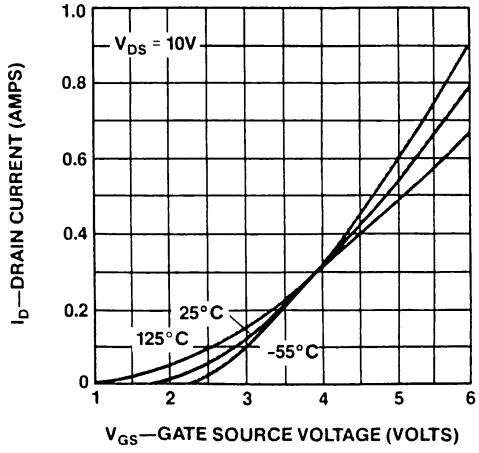


FIGURE 3. Temperature Effects on $r_{DS(on)}$

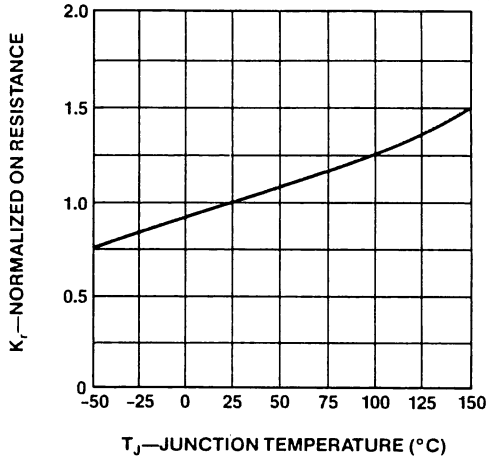


FIGURE 4. Threshold Region

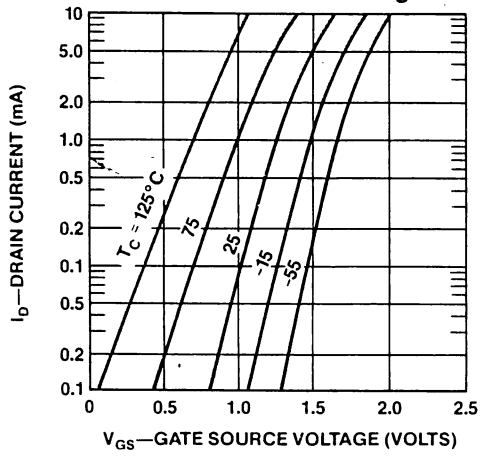
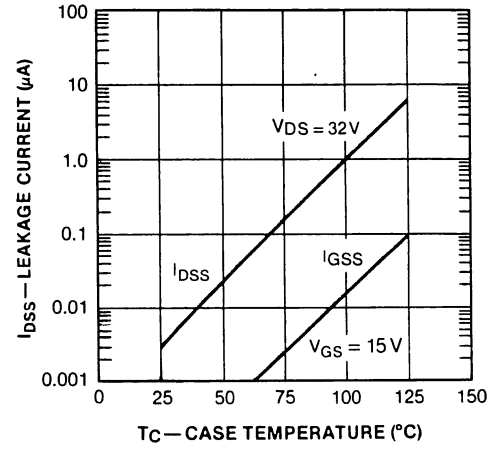


FIGURE 5. Off-State Current



TRANSIENT THERMAL RESPONSE CURVES

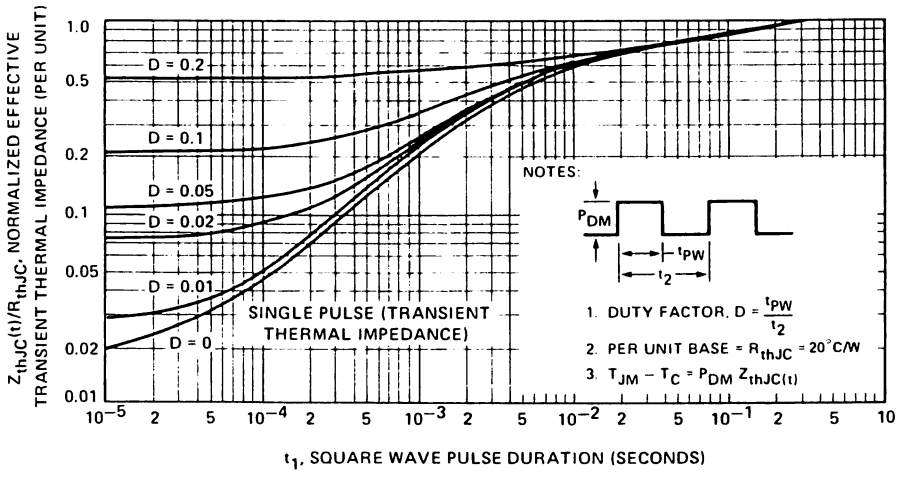
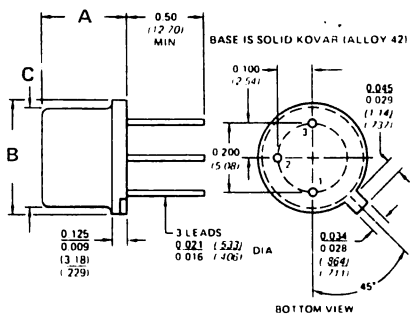
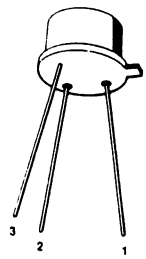


FIGURE 1. TO-39 Package

TO-205 (TO-39)
PACKAGE SUFFIX B





All Dimensions in Inches
(All Dimensions in Millimeters)

Package	Dimension A		Dimension B		Dimension C	
T0–205AD	0.260 / 0.240	*(6.60) / (6.10)*	0.370 / 0.335	*(9.39) / (8.51)*	0.335 / 0.305	*(8.50) / (7.75)*
T0–205AF	0.180 / 0.160	*(4.57) / (4.07)*	0.370 / 0.340	*(9.39) / (8.64)*	0.355 / 0.315	*(9.01) / (8.01)*